



# M74HC367

## HEX BUS BUFFER WITH 3 STATE OUTPUT NON INVERTING

- HIGH SPEED:  
 $t_{PD} = 9\text{ns}$  (TYP.) at  $V_{CC} = 6\text{V}$
- LOW POWER DISSIPATION:  
 $I_{CC} = 4\mu\text{A}$ (MAX.) at  $T_A=25^\circ\text{C}$
- HIGH NOISE IMMUNITY:  
 $V_{NIH} = V_{NIL} = 28\%$   $V_{CC}$  (MIN.)
- SYMMETRICAL OUTPUT IMPEDANCE:  
 $|I_{OH}| = I_{OL} = 6\text{mA}$  (MIN)
- BALANCED PROPAGATION DELAYS:  
 $t_{PLH} \approx t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE:  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 367



### ORDER CODES

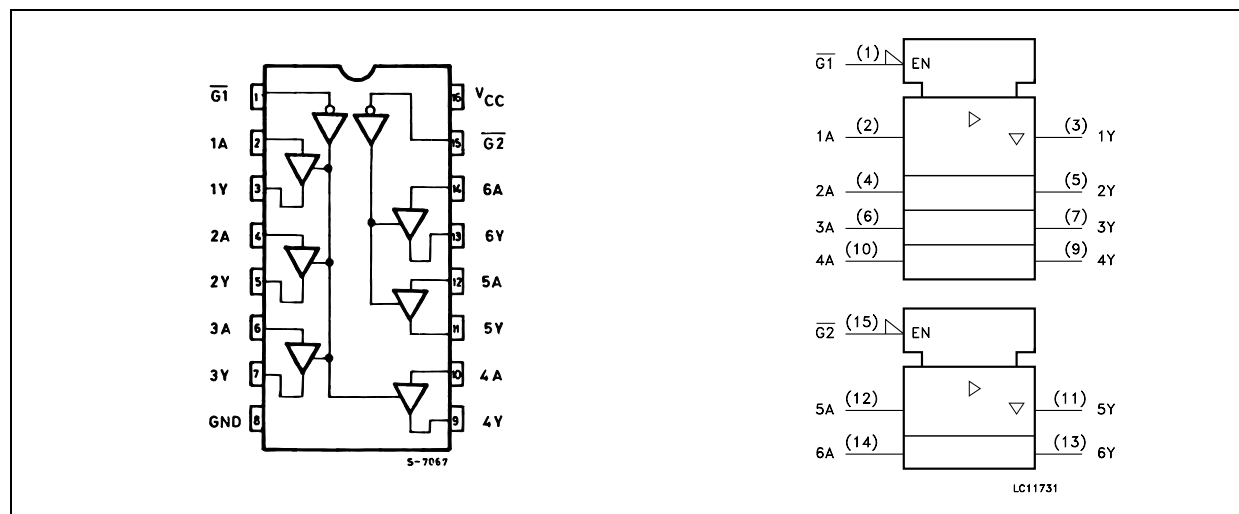
PACKAGE	TUBE	T & R
DIP	M74HC367B1R	
SOP	M74HC367M1R	M74HC367RM13TR
TSSOP		M74HC367TTR

### DESCRIPTION

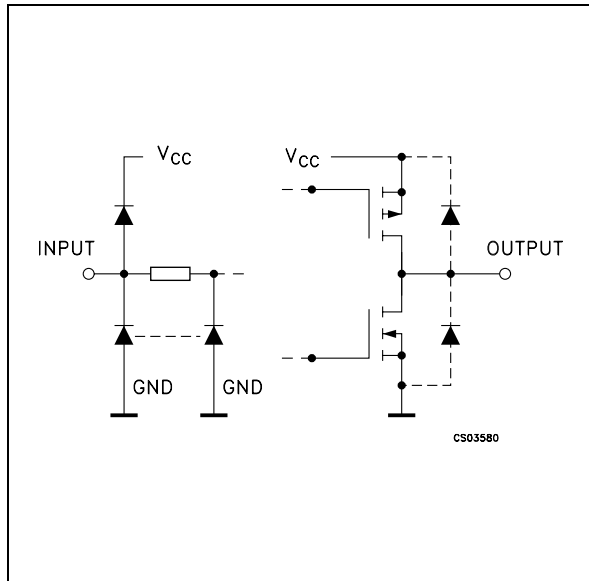
The M74HC367 is an high speed CMOS HEX BUS BUFFER 3-STATE OUTPUTS fabricated with silicon gate C<sup>2</sup>MOS technology. This device contains six buffers, four buffers are controlled by an enable input ( $\overline{G1}$ ) and the other two buffers are controlled by the other enable input ( $\overline{G2}$ ); the outputs of each buffer group are

enabled when  $\overline{G1}$  and/or  $\overline{G2}$  inputs are held low, and when held high, these outputs are disabled in a high-impedance state. All inputs are equipped with protection circuits against static discharge and transient excess voltage.

### PIN CONNECTION AND IEC LOGIC SYMBOLS



**INPUT AND OUTPUT EQUIVALENT CIRCUIT**



**PIN DESCRIPTION**

PIN No	SYMBOL	NAME AND FUNCTION
1, 15	$\overline{G1}, \overline{G2}$	3 State Output Enable Input
2, 4, 6, 10, 12, 14	1A to 6A	Data Inputs
3, 5, 7, 9, 11, 13	1Y to 6Y	Data Outputs
8	GND	Ground (0V)
16	V <sub>CC</sub>	Positive Supply Voltage

**TRUTH TABLE**

INPUTS		OUTPUTS
$\overline{G}$	A <sub>n</sub>	Y <sub>n</sub>
L	L	L
L	H	H
H	X	Z

X: Don't Care  
Z: High Impedance

**ABSOLUTE MAXIMUM RATINGS**

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to +7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Current	± 35	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 70	mA
P <sub>D</sub>	Power Dissipation	500(*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to +150	°C
T <sub>L</sub>	Lead Temperature (10 sec)	300	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied

(\*) 500mW at 65 °C; derate to 300mW by 10mW/°C from 65°C to 85°C

**RECOMMENDED OPERATING CONDITIONS**

Symbol	Parameter	Value	Unit	
V <sub>CC</sub>	Supply Voltage	2 to 6	V	
V <sub>I</sub>	Input Voltage	0 to V <sub>CC</sub>	V	
V <sub>O</sub>	Output Voltage	0 to V <sub>CC</sub>	V	
T <sub>op</sub>	Operating Temperature	-55 to 125	°C	
t <sub>r</sub> , t <sub>f</sub>	Input Rise and Fall Time	V <sub>CC</sub> = 2.0V	0 to 1000	ns
		V <sub>CC</sub> = 4.5V	0 to 500	ns
		V <sub>CC</sub> = 6.0V	0 to 400	ns

## DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V <sub>CC</sub> (V)		T <sub>A</sub> = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V <sub>IH</sub>	High Level Input Voltage	2.0		1.5			1.5		1.5		V
		4.5		3.15			3.15		3.15		
		6.0		4.2			4.2		4.2		
V <sub>IL</sub>	Low Level Input Voltage	2.0				0.5		0.5		0.5	V
		4.5				1.35		1.35		1.35	
		6.0				1.8		1.8		1.8	
V <sub>OH</sub>	High Level Output Voltage	2.0	I <sub>O</sub> =-20 μA	1.9	2.0		1.9		1.9		V
		4.5	I <sub>O</sub> =-20 μA	4.4	4.5		4.4		4.4		
		6.0	I <sub>O</sub> =-20 μA	5.9	6.0		5.9		5.9		
		4.5	I <sub>O</sub> =-6.0 mA	4.18	4.31		4.13		4.10		
		6.0	I <sub>O</sub> =-7.8 mA	5.68	5.8		5.63		5.60		
V <sub>OL</sub>	Low Level Output Voltage	2.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	V
		4.5	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		6.0	I <sub>O</sub> =20 μA		0.0	0.1		0.1		0.1	
		4.5	I <sub>O</sub> =6.0 mA		0.17	0.26		0.33		0.40	
		6.0	I <sub>O</sub> =7.8 mA		0.18	0.26		0.33		0.40	
I <sub>I</sub>	Input Leakage Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			± 0.1		± 1		± 1	μA
I <sub>OZ</sub>	High Impedance Output Leakage Current	6.0	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub> V <sub>O</sub> = V <sub>CC</sub> or GND			± 0.5		± 5		± 10	μA
I <sub>CC</sub>	Quiescent Supply Current	6.0	V <sub>I</sub> = V <sub>CC</sub> or GND			4		40		80	μA

**AC ELECTRICAL CHARACTERISTICS** ( $C_L = 50 \text{ pF}$ , Input  $t_r = t_f = 6\text{ns}$ )

Symbol	Parameter	Test Condition			Value						Unit	
		$V_{CC}$ (V)	$C_L$ (pF)		$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$t_{TLH} \ t_{THL}$	Output Transition Time	2.0	50			25	60		75		90	ns
		4.5				7	12		15		18	
		6.0				6	10		13		15	
$t_{PLH} \ t_{PHL}$	Propagation Delay Time	2.0	50			30	85		105		130	ns
		4.5				10	17		21		26	
		6.0				9	14		18		22	
		2.0	150			42	105		130		160	ns
		4.5				14	21		26		32	
		6.0				12	18		22		27	
$t_{PZL} \ t_{PZH}$	High Impedance Output Enable Time	2.0	50	$R_L = 1 \text{ K}\Omega$		36	90		115		135	ns
		4.5				11	18		23		27	
		6.0				9	15		20		23	
		2.0	150			49	110		140		165	ns
		4.5				15	22		28		33	
		6.0				13	19		24		28	
$t_{PLZ} \ t_{PHZ}$	High Impedance Output Disable Time	2.0	50	$R_L = 1 \text{ K}\Omega$		32	95		120		145	ns
		4.5				14	19		24		29	
		6.0				12	16		20		25	

**CAPACITIVE CHARACTERISTICS**

Symbol	Parameter	Test Condition			Value						Unit	
		$V_{CC}$ (V)			$T_A = 25^\circ\text{C}$			$-40 \text{ to } 85^\circ\text{C}$		$-55 \text{ to } 125^\circ\text{C}$		
					Min.	Typ.	Max.	Min.	Max.	Min.		Max.
$C_{IN}$	Input Capacitance					5	10		10		10	pF
$C_{PD}$	Power Dissipation Capacitance (note 1)					33						pF

1)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation.  $I_{CC(opr)} = C_{PD} \times V_{CC} \times f_{IN} + I_{CC}/6$  (per Channel)

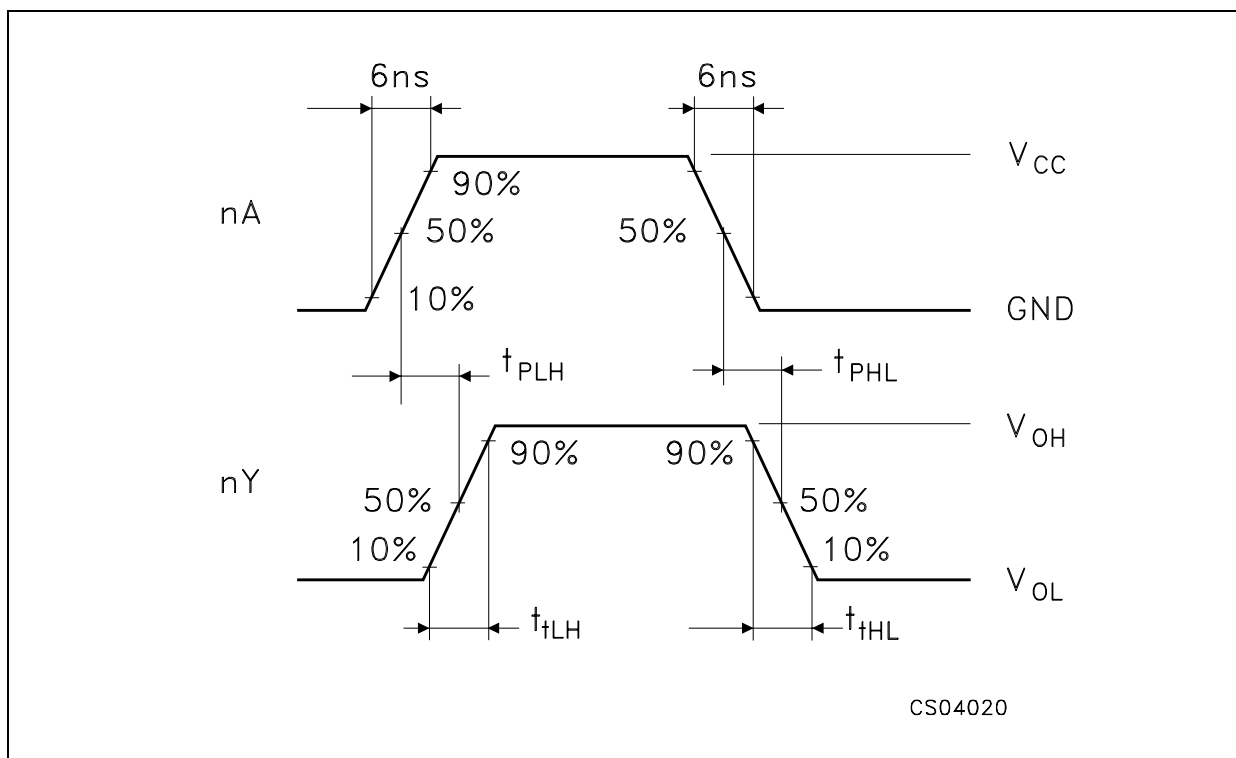
TEST CIRCUIT



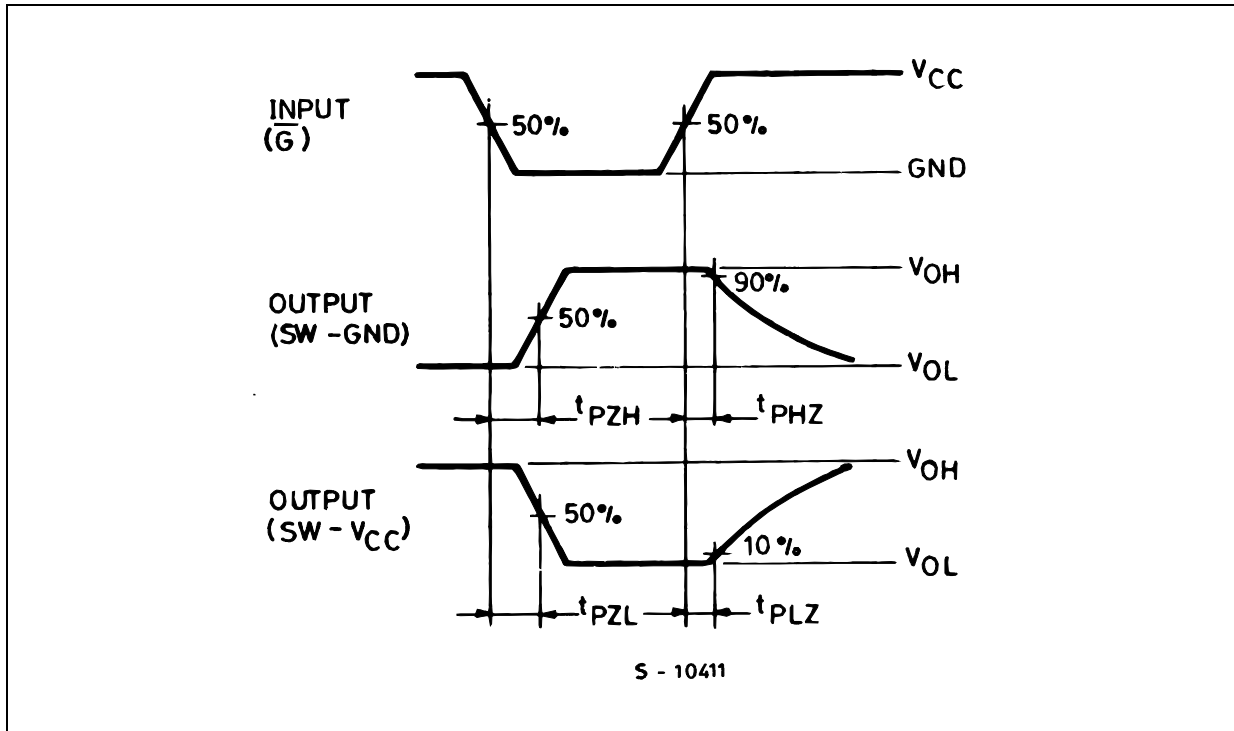
TEST	SWITCH
$t_{PLH}$ , $t_{PHL}$	Open
$t_{PZL}$ , $t_{PLZ}$	$V_{CC}$
$t_{PZH}$ , $t_{PHZ}$	GND

$C_L = 50\text{pF}/150\text{pF}$  or equivalent (includes jig and probe capacitance)  
 $R_1 = 1\text{K}\Omega$  or equivalent  
 $R_T = Z_{OUT}$  of pulse generator (typically  $50\Omega$ )

WAVEFORM 1: PROPAGATION DELAY TIMES ( $f=1\text{MHz}$ ; 50% duty cycle)



WAVEFORM 2: OUTPUT ENABLE AND DISABLE TIMES (f=1MHz; 50% duty cycle)



### Plastic DIP-16 (0.25) MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
a1	0.51			0.020		
B	0.77		1.65	0.030		0.065
b		0.5			0.020	
b1		0.25			0.010	
D			20			0.787
E		8.5			0.335	
e		2.54			0.100	
e3		17.78			0.700	
F			7.1			0.280
I			5.1			0.201
L		3.3			0.130	
Z			1.27			0.050



**SO-16 MECHANICAL DATA**

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	9.8		10	0.385		0.393
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		8.89			0.350	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.62			0.024
S	8° (max.)					



PO13H



## TSSOP16 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved  
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco  
Singapore - Spain - Sweden - Switzerland - United Kingdom

© <http://www.st.com>